

The PECVD system is a 13.56 MHz driven parallel plate reactor with manual sample loading and a heated substrate electrode. It can be used for device quality deposition of Si, SiO<sub>2</sub> and Si<sub>3</sub>N<sub>4</sub> films on substrates. The substrate platen can be heated up to 400° C during deposition. This is a capability that greatly enhanced our research efforts at MSU and opens the possibility of many lithography processes, and device structures previously not possible.